REMARKS

At the outset, the Examiner is thanked for the thorough review and consideration of the pending application. The Office Action dated December 3, 2007, has been received and its contents carefully reviewed.

By this Response, claim 1 has been amended without prejudice or disclaimer of the subject matter recited therein. No new matter has been added. Accordingly, claims 1-2 and 5-6 remain pending in this application. Reexamination and reconsideration of the pending claims are respectfully requested.

In the Office Action, claim 1 is objected. The objection of claim 1 is respectfully traversed and reconsideration is requested.

In the Office Action, claims 1, 2 and 5-6 are rejected under 35 U.S.C. § 103(a) as being unpatentable over U.S. Patent No. 6,380,559B1 to Park et al. (hereinafter "Park") in view of U.S. Patent No. 6,255,130 B1 to Kim 130 (hereinafter "Kim 130"), and further in view of U.S. Patent No. 6,429,057B1 to Hong et al. (hereinafter "Hong") and U.S. Patent No. 5,517,342 to Kim 342 et al. (hereinafter "Kim 342"). Claim 3 is rejected under 35 U.S.C. § 103(a) as being unpatentable over Park, Hong and Kim and further in view of U.S. Patent No. 6,255,130B1 to Kim et al. (hereinafter "Kim 130").

The rejection of claims 1, 2, 5 and 6 is respectfully traversed and reconsideration is requested. Claims 1, 2, 5 and 6 are allowable over the cited references in that each of these claims recites a combination of elements including, for example, "preparing a cutting-off plate having an opening region overlapped with the pad part of the substrate to expose the pad part of the substrate and a cutting-off region overlapped with a remainder part other than the pad part of the substrate, wherein the cutting-off plate of cutting-off region is formed by a metal other than molybdenum" and "exposing entire surface of the gate pad and the data pad protection electrode of the pad part by a etching process using etching gas passing through opening region of the cutting-off plate without forming a photoresist pattern". None of the cited references including Park, Hong, Kim 342 and Kim 130 singly or in combination, teaches or suggests at least this feature of the claimed invention. In particular, and as discussed in the Examiner interview of February 28, 2007, the dry etching process in paragraph [0101] is different than "exposing entire surface of the gate pad and the data pad protection electrode of the pad part by a etching process

using etching gas passing through opening region of the cutting-off plate without forming a photoresist pattern". Accordingly, Applicants respectfully request that the objection to the claim be withdrawn.

The claimed invention includes the cutting-off plate having an opening region overlapped with the pad part of the substrate to expose the pad part of the substrate and a cutting-off region overlapped with a remainder part other than the pad part of the substrate. In the claimed invention, the etching gas passes through the opening region of the cutting-off plate.

But, Park includes the mask having a transparent substrate 610 and light transmission control film 620 and an opaque film 630(See Fig, 31). In Park, etching gas does not pass through the B portion(correspondent with opening region of the present invention) of the mask because the etching gas does not pass through the transparent substrate 610 of B portion.

In Kim 130, the photo mask shown Fig. 7B is simplified the general photo mask. The photo mask shown Fig. 7 needs the substrate as the photo mask shown Fig. 40A. A plurality of silt patterns 413 is independently formed, as shown Fig. 39C. To support the plurality of silt patterns, it needs substrate formed under the plurality of silt patterns.

Accordingly, in Kim 130, etching gas does not pass through the opening region of the mask because the etch gas does not pass through the transparent substrate of the mask.

In Hong and Kim 342, etching gas does not pass through the opening region of the mask because the etching gas does not pass through the transparent substrate of the mask.

Accordingly, Applicant respectfully submits that claim 1 and claims 2, 5 and 6, which depend from claim 1, are allowable over the cited references.

Applicants believe the foregoing amendments place the application in condition for allowance and early, favorable action is respectfully solicited.

If for any reason the Examiner finds the application other than in condition for allowance, the Examiner is requested to call the undersigned attorney at (202) 496-7500 to discuss the steps necessary for placing the application in condition for allowance. All correspondence should continue to be sent to the below-listed address.

If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. § 1.136, and any additional fees required under 37 C.F.R. § 1.136 for any necessary extension of time, or any other fees required to complete the filing of this response, may be charged to Deposit Account No. 50-0911. Please credit any overpayment to deposit Account No. 50-0911. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

Dated: 3 March 2008

By

Registration No. 40,106

McKENNA LONG & ALDRIDGE LLP

1900 K Street, N.W. Washington, DC 20006

(202) 496-7500

Attorneys for Applicant